



ALPHA & OMEGA
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AOS Semiconductor Product Reliability Report

AON4605, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

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This AOS product reliability report summarizes the qualification result for AON4605. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AON4605 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

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I. Product Description:

The AON4605 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications.

Details refer to the datasheet.

II. Die / Package Information:

	AON4605
Process	Standard sub-micron 30V Complementary MOSFET
Package Type	DFN 3x2A
Lead Frame	Bare Cu
Die Attach	Ag Epoxy
Bond	Au wire
Mold Material	Epoxy resin with silica filler
Moisture Level	Up to Level 1

III. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
HTRB	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
MSL Precondition	168hr 85°C / 85%RH + 3 cycle reflow@260°C (MSL 1)	-	2772 pcs	0	JESD22-A113
HAST	130°C , 85%RH, 33.3 psi, Vds = 80% of Vdsmax	96 hours	924 pcs	0	JESD22-A110
Autoclave	121°C , 29.7psi, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air,	250 / 500 cycles	924 pcs	0	JESD22-A104

Note: The reliability data presents total of available generic data up to the published date.

IV. Reliability Evaluation

FIT rate (per billion): 3.43

MTTF = 33270 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $\text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 3.43$

MTTF = $10^9 / \text{FIT} = 33270$ years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from burn-in tests

H = Duration of burn-in testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [**Af**] = $\text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, $8.617164 \times 10^{-5} \text{eV} / \text{K}$